

setting said substrate onto a stage having a flat surface in such a manner that a lower surface of said substrate is in contact with said stage;

flattening said substrate by vacuum-sucking said lower surface of said substrate; and

irradiating said semiconductor film with a laser beam having a cross section which is elongated in one direction while relatively moving said substrate with respect to said laser beam, and while vacuum-sucking said lower surface of said substrate.

9. (Amended) A method according to claim 7 wherein said semiconductor device is a liquid crystal display device.

10. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over an upper surface of a substrate;

setting said substrate onto a stage having a flat surface and at least one suction inlet in such a manner that a lower surface of said substrate is in contact with said stage;

flattening said substrate by vacuum-sucking said lower surface of said substrate; and

irradiating said semiconductor film with a laser beam having a cross section which is elongated in one direction while relatively moving said substrate with respect to said laser beam, and while vacuum-sucking said lower surface of said substrate.

12. (Amended) A method according to claim 10 wherein said semiconductor device is a liquid crystal display device.

50113 } 13. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over a lower surface of a substrate;

heating said semiconductor film;

setting said substrate onto a stage having a flat surface in such a manner that a lower surface of said substrate is in contact with said stage;

flattening said substrate by vacuum-sucking said lower surface of said substrate; and

irradiating said semiconductor film with a laser beam having a cross section which is elongated in one direction while relatively moving said substrate with respect to said laser beam, and while vacuum-sucking said lower surface of said substrate.

15. (Amended) A method according to claim 13 wherein said semiconductor device is a liquid crystal display device.

54 } 16. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over an upper surface of a substrate;

heating said semiconductor film;

setting said substrate onto a stage having a flat surface and at least one suction inlet in such a manner that a lower surface of said substrate is in contact with said stage;

flattening said substrate by vacuum-sucking said lower surface of said substrate; and

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irradiating said semiconductor film with a laser beam having a cross section which is elongated in one direction while relatively moving said substrate with respect to said laser beam, and while vacuum-sucking said lower surface of said substrate.

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18. (Amended) A method according to claim 16 wherein said semiconductor device is a liquid crystal display device.

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19. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over an upper surface of a substrate;

heating said substrate to crystallize said semiconductor film;

setting said substrate onto a stage having a flat surface in such a manner that a lower surface of said substrate is in contact with said stage;

flattening said substrate by vacuum-sucking said lower surface of said substrate; and

irradiating the crystallized semiconductor film over said substrate provided on said stage with a laser beam having a cross section which is elongated in one direction while relatively moving said substrate with respect to said laser beam, and while vacuum-sucking said lower surface of said substrate.

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21. (Amended) A method according to claim 19 wherein said semiconductor device is a liquid crystal display device.

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22. (Amended) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over an upper surface of a substrate;

heating said substrate to crystallize said semiconductor film;

setting said substrate onto a stage having a flat surface and at least one suction inlet in such a manner that a lower surface of said substrate is in contact with said stage;

flattening said substrate by vacuum-sucking said lower surface of said substrate; and

irradiating the crystallized semiconductor film with a laser beam having a cross section which is elongated in one direction while relatively moving said substrate with respect to said laser beam, and while vacuum-sucking said lower surface of said substrate.

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24. (Amended) A method according to claim 22 wherein said semiconductor device is a liquid crystal display device.

Please add claims 45, 46, 47, 48, 49, 50, 51, 52, 53, 54, 55, 56, 57, 58, 59, and 60.

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--45. (New) A method according to claim 7 wherein an entire surface of said semiconductor film is irradiated by said laser beam.

46. (New) A method according to claim 10 wherein an entire surface of said semiconductor film is irradiated by said laser beam.

47. (New) A method according to claim 13 wherein an entire surface of said semiconductor film is irradiated by said laser beam.

48. (New) A method according to claim 16 wherein an entire surface of said semiconductor film is irradiated by said laser beam.

49. (New) A method according to claim 19 wherein an entire surface of said semiconductor film is irradiated by said laser beam.

50. (New) A method according to claim 22 wherein an entire surface of said semiconductor film is irradiated by said laser beam.

51. (New) A method of manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film over an upper surface of a substrate;

setting said substrate onto a stage having a flat surface in such a manner that a lower surface of said substrate is in contact with said stage;

flattening said substrate by vacuum-sucking said lower surface of said substrate; and

irradiating said semiconductor film with a laser beam while relatively moving said substrate with respect to said laser beam, and while vacuum-sucking said lower surface of said substrate.

52. (New) A method according to claim 51 wherein said laser beam is an excimer laser beam.

53. (New) A method according to claim 51 wherein an entire surface of said semiconductor film is irradiated by said laser beam.

54. (New) A method according to claim 51 wherein said substrate is a glass substrate.

55. (New) A method according to claim 51 wherein said semiconductor device is a liquid crystal display device.

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*Cont* 56. (New) A method of manufacturing a semiconductor device comprising the steps of:  
forming a semiconductor film over an upper surface of a substrate;  
heating said semiconductor film;  
setting said substrate onto a stage having a flat surface in such a manner that a lower surface of said substrate is in contact with said stage;  
flattening said substrate by vacuum-sucking said lower surface of said substrate; and  
irradiating said semiconductor film with a laser beam while relatively moving said substrate with respect to said laser beam, and while vacuum-sucking said lower surface of said substrate.

57. (New) A method according to claim 56 wherein said laser beam is an excimer laser beam.

58. (New) A method according to claim 56 wherein an entire surface of said semiconductor film is irradiated by said laser beam.

59. (New) A method according to claim 56 wherein said substrate is a glass substrate.

60. (New) A method according to claim 56 wherein said semiconductor device is a liquid crystal display device.--

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